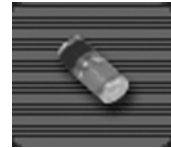
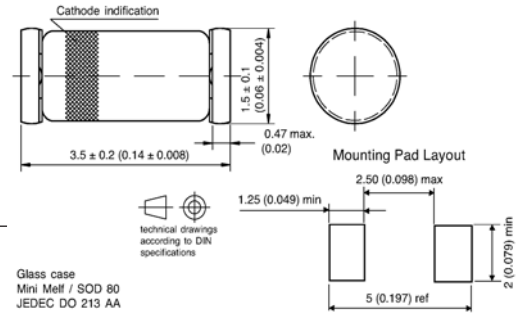


Features

- ◆ Silicon Epitaxial Planar Diode
- ◆ Fast switching diode in MiniMELF case especially suited for automatic insertion.
- ◆ This diode is also available in other case styles including the DO-35 case with the type designation 1N4448.

Mechanical Data

- ◆ Case: MiniMELF Glass Case (SOD-80)
- ◆ Weight: approx. 0.05g
- ◆ Cathode Band Color: Black



Maximum Ratings and Thermal Characteristics

($T_A=25^\circ\text{C}$ unless otherwise noted.)

Parameter	Symbol	Limit	Unit
Reverse voltage	V_R	75	Volts
Peak reverse voltage	V_{RM}	100	Volts
Average rectified current half wave rectification with resistive load at $T_{amb}=25^\circ\text{C}$ ⁽¹⁾	$I_{F(AV)}$	150	mA
Surge forward current at $t < 1\text{s}$ and $T_J=25^\circ\text{C}$	I_{FSM}	500	mA
Power dissipation at $T_{amb}=25^\circ\text{C}$ ⁽¹⁾	P_{tot}	500	mW
Thermal resistance junction to ambient air ⁽¹⁾	$R_{\theta JA}$	350	$^\circ\text{C/W}$
Junction temperature	T_J	175	$^\circ\text{C}$
Storage temperature range	T_S	-65 to +175	$^\circ\text{C}$

Electrical Characteristics

($T_J=25^\circ\text{C}$ unless otherwise noted.)

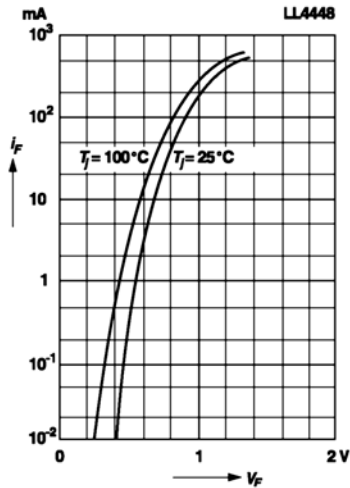
Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Forward voltage	V_F	$I_F=5\text{mA}$ $I_F=100\text{mA}$	0.62 -	- -	0.72 1.0	Volt
Leakage current	I_R	$V_R=20\text{V}$ $V_R=75\text{V}$ $V_R=20\text{V}, T_J=150^\circ\text{C}$	- - -	- - -	25 5.0 50	μA
Capacitance	C_{tot}	$V_F=V_R=0\text{V}$	-	-	4.0	pF
Reverse recovery time	t_r	$I_F=10\text{mA}, I_R=1\text{mA}$ $V_R=6\text{V}, R_L=100\Omega$	-	-	4.0	ns
Rectification efficiency (see third Page)	η_v	$f=100\text{MHz}, V_{RF}=2\text{V}$	0.45	-	-	-

Notes: 1. Valid provided that electrodes are kept at ambient temperature

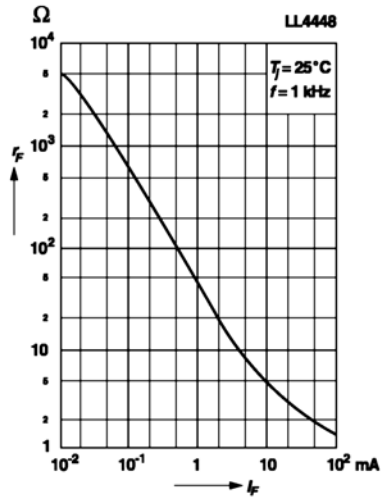
RATINGS AND CHARACTERISTIC CURVES

($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Forward characteristics

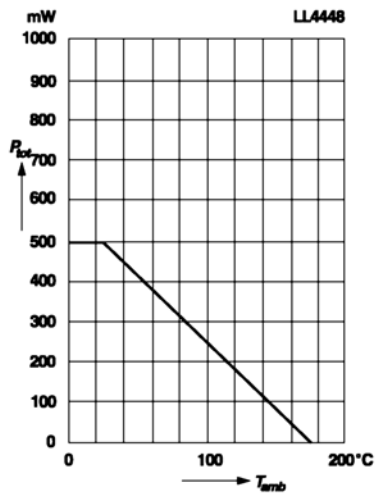


Dynamic forward resistance versus forward current

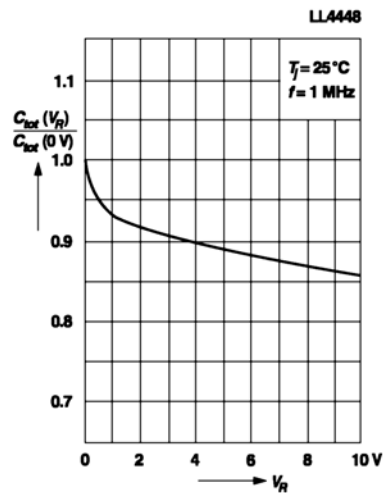


Admissible power dissipation versus ambient temperature

Valid provided that electrodes are kept at ambient temperature



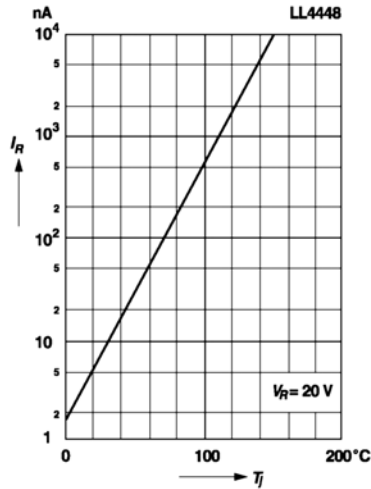
Relative capacitance versus reverse voltage



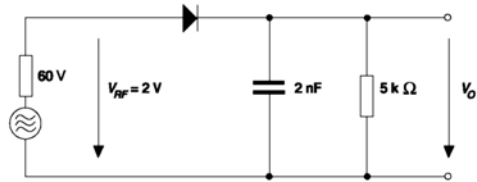
RATINGS AND CHARACTERISTIC CURVES

($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Leakage current versus junction temperature



Rectification Efficiency Measurement Circuit



Admissible repetitive peak forward current versus pulse duration

Valid provided that electrodes are kept at ambient temperature

